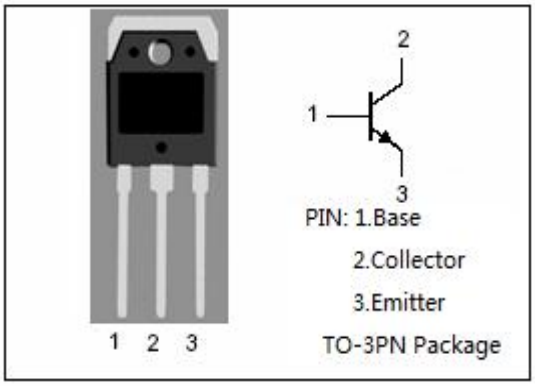
isc Silicon NPN Power Transistor — BUV47A

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= 450V(Min.)
- Collector-Emitter Saturation Voltage-
  :$V_{CE(sat)}$= 1.5V(Max.)@I_C= 5A
- High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

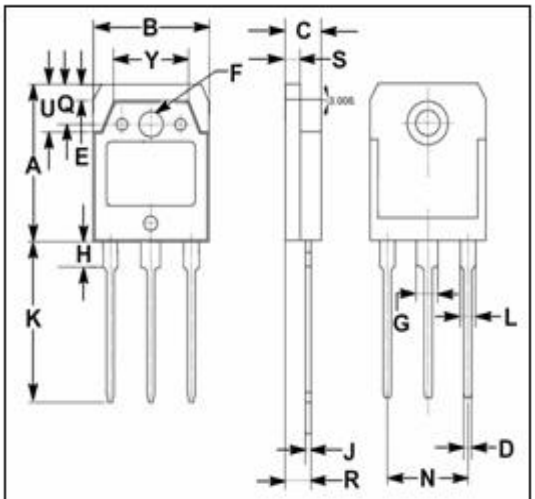
- Designed for 220V switchmode power supply, DC and AC motor control applications.

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1000	V
V_{CEO}	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	9	A
I_{CM}	Collector Current-Peak	15	A
I_B	Base Current-Continuous	8	A
I_{BM}	Base Current-Peak	10	A
P_C	Collector Power Dissipation @T_C=25℃	100	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.25	℃/W



DIM	mm MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA; I_B= 0	450			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 50mA; I_C= 0	7			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 5A; I_B= 1A			1.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 8A; I_B= 2.5A			3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 5A; I_B= 1A			1.6	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 1000V ; I_B= 0			0.15	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			1.0	mA